

**32 Mbit Mobile FCRAM™
3.0 V, Page Mode
MB82DP02183E-65L**

■ **FEATURES**

- Pseudo SRAM with Asynchronous SRAM Interface
- 8 Words Page Read Access Capability
- Byte Control by \overline{LB} , \overline{UB}
- Low Power Consumption
- Various Power Down Mode
 - Sleep
 - 4 Mbit Partial
 - 8 Mbit Partial
- Chip / Wafer Business

■ **MAIN SPECIFICATIONS**

| | | |
|---------------------------------|-------------------|-------|
| Part Number | MB82DP02183E-65L | |
| Organization | 2 M Word × 16 bit | |
| Supply Voltage | 2.6 V to 3.1 V | |
| Page Address Access Time (Max.) | 20 ns | |
| Address Access Time (Max.) | 65 ns | |
| Active Current (Max.) | 30 mA | |
| Standby Current (Max.) | 120 μA | |
| Power Down Current (Max.) | Sleep | 10 μA |

Note: FCRAM is a trademark of Fujitsu Limited, Japan.

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